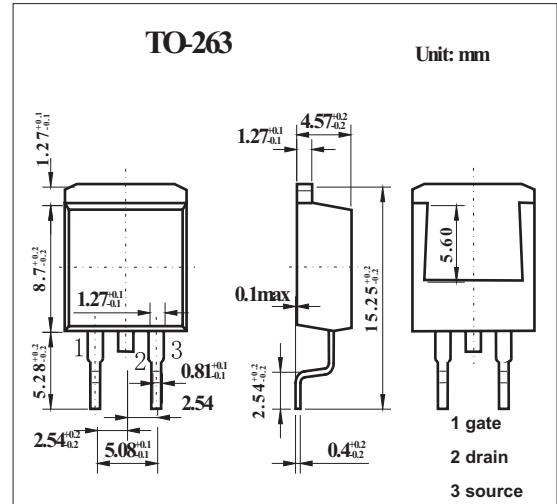


KUK7107-55ATE

■ Features

- Integrated temperature sensor
- ESD protection
- Q101 compliant
- Standard level compatible



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain-source voltage	V _{DS}	55	V
Drain-gate voltage I _{DG} = 250 μA	V _{DGR}	55	V
Gate-source voltage	V _{GS}	±20	V
Drain current (DC) T _{mb} = 25°C, V _{GS} = 10 V	I _D	140	A
Drain current (DC) T _{mb} = 100°C, V _{GS} = 10 V	I _D	75	A
peak drain current *1	I _{DM}	560	A
Total power dissipation T _{mb} = 25°C	P _{tot}	272	W
gate-source clamping current (continuous)	I _{GS(CL)}	10	mA
gate-source clamping current *3		50	mA
FET to temperature sense diode isolation voltage	V _{isol(FET-TSD)}	±100	V
Storage & operating temperature	T _{stg} , T _j	-55 to 175	°C
reverse drain current (DC) T _{mb} = 25°C	I _{DR}	140	A
		75	A
pulsed reverse drain current *1	I _{DRM}	560	A
non-repetitive avalanche energy *2	E _{DS(AL)S}	460	J
Thermal resistance junction to mounting base	R _{th j-mb}	0.55	K/W
Thermal resistance junction to ambient	R _{th j-a}	50	K/W

* 1 T_{mb} = 25°C; pulsed; t_p ≤ 10 μs;

*2 unclamped inductive load; I_D = 68 A; V_{DS} ≤ 55 V; V_{GS} = 10 V; R_{GS} = 50Ω; starting T_j = 25°C

*3 t_p = 5 ms; δ = 0.01

*4 Human Body Model; C = 100 pF; R = 1.5 kΩ

KUK7107-55ATE

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
drain-source breakdown voltage	V _{(BR)DSS}	I _D = 0.25 mA; V _{GS} = 0 V; T _J = 25°C	55			V
		I _D = 0.25 mA; V _{GS} = 0 V; T _J = -55°C	50			V
gate-source threshold voltage	V _{GS(th)}	I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 25°C	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 175°C	1			V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _J = -55°C			4.4	V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 55 V; V _{GS} = 0 V; T _J = 25°C		0.1	10	μA
		V _{DS} = 55 V; V _{GS} = 0 V; T _J = 175°C			250	μA
gate-source breakdown voltage	V _{(BR)GSS}	I _G = ±1 mA; -55°C < T _J < 175°C	20	22		V
gate-source leakage current	I _{GSS}	V _{GS} = ±10 V; V _{DS} = 0 V; T _J = 25°C		22	1000	nA
		V _{GS} = ±10 V; V _{DS} = 0 V; T _J = 175°C			10	μA
drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V; I _D = 50 A; T _J = 25°C		5.8	7	mΩ
		V _{GS} = 10 V; I _D = 50 A; T _J = 175°C			14	mΩ
forward voltage, temperature sense diode	V _F	I _F = 250 mA	648	658	668	mV
temperature coefficient temperature sense diode	S _F	I _F = 250 mA; -55°C < T _J < 175°C	-1.4	-1.54	-1.68	mV/K
temperature sense diode forward voltage hysteresis	V _{hys}	125 μA < I _F < 250 μA	25	32	50	mV
total gate charge	Q _{g(tot)}	V _{GS} = 10 V; V _{DD} = 44 V; I _D = 25 A		116		nC
gate-to-source charge	Q _{gs}			19		nC
gate-to-drain (Miller) charge	Q _{gd}			50		nC
input capacitance	C _{iss}			4500		pF
output capacitance	C _{oss}	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz		960		pF
reverse transfer capacitance	C _{rss}			510		pF
turn-on delay time	t _{d(on)}			36		ns
rise time	t _r	V _{DD} = 30 V; R _L = 1.2Ω; V _{GS} = 10 V; R _G = 10Ω		115		ns
turn-off delay time	t _{d(off)}			159		ns
fall time	t _f			111		ns
internal drain inductance	L _d	measured from upper edge of drain mounting base to center of die		2.5		nH
internal source inductance	L _s	measured from source lead to source bond pad		7.5		nH
source-drain (diode forward) voltage	V _{SD}	I _s = 25A; V _{GS} = 0 V		0.85	1.2	V
reverse recovery time	t _{rr}	I _s = 20 A; diF/dt = -100 A/μs;		80		ns
recovered charge	Q _r	V _{GS} = -10 V; V _{DS} = 30 V		200		nC